
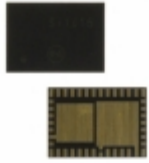
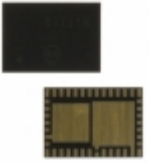
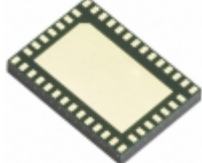


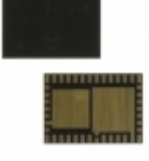
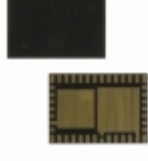
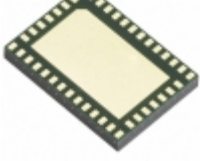
	<h2>SI1011X-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI1011X-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 12V SC-89</p> <p>Datenblätter:  SI1011X-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 51000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1011X-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 12V SC-89
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	51000 pcs Stock
detaillierte Beschreibung	P-Channel 12V 190mW (Ta) Surface Mount SC-89-3
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SC-89, SOT-490
Supplier Device-Gehäuse	SC-89-3
Verlustleistung (max)	190mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	-
Rds On (Max) @ Id, Vgs	640 mOhm @ 400mA, 4.5V
VGS (th) (Max) @ Id	800mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	4nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	62pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	1.2V, 4.5V
Vgs (Max)	±5V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1011X-T1-GE3CT

SI1011X-T1-GE3 ist neu im Original, Suche SI1011X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1011X-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1011X-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1011-C-GM2 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>	 <p>SI1012-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-WFQFN</p>	 <p>SI1012-C-GM2R Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>	 <p>SI1010DK Energy Micro (Silicon Labs) DEVELOPMENT KIT SI101X</p>
 <p>SI1011X-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V SC-89</p>	 <p>SI1012-C-GM2 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>	 <p>SI1012-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-WFQFN</p>	 <p>SI1011-C-GM2R Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>

heiße Teile

Mehr

SI1000-C-GM	SI1002-C-GMR	SI1003-C-GM	SI1011X-T1-GE3	SI1012CR-T1-GE3
SI1012CR-T1-GE3	SI1012R-T1	SI1012R-T1-E3	SI1012R-T1-E3	SI1012R-T1-GE3
SI1012R-T1-GE3	SI1012X-T1	SI1012X-T1-E3	SI1012X-T1-E3	SI1012X-T1-GE3
SI1012X-T1-GE3	SI1013CX-T1-GE3	SI1013CX-T1-GE3	SI1013R-T1	SI1013R-T1-E3
SI1013R-T1-E3	SI1013R-T1-GE3	SI1013R-T1-GE3	SI1013X-T1	SI1013X-T1-E3
SI1013X-T1-E3	SI1013X-T1-GE3	SI1013X-T1-GE3	SI1016CX-T1-GE3	SI1016CX-T1-GE3
SI1016X-T1-E3	SI1016X-T1-E3	SI1016X-T1-GE3	SI1016X-T1-GE3	SI1016X2-T1-GE3
SI1021R-T1	SI1021R-T1-E3	SI1021R-T1-E3	SI1022R-T1	SI1022R-T1-E3
SI1022R-T1-E3	SI1022R-T1-GE3	SI1022R-T1-GE3	SI1022R-T1-E3	SI1023CX-T1-GE3
SI1023CX-T1-GE3	SI1023X-T1	SI1023X-T1-E3	SI1023X-T1-E3	SI1023X-T1-GE3

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